L Number			DB	Time stamp
1	240		USPAT;	2003/12/09 12:45
7		chen-tsung-chuanin. chen-t-c.in.	US-PGPUB;	
		hsu-shew-tsuin. hsu-s-tin.	EPO; JPO;	
	7100	430/311 313 314 317 327 333 333	DERWENT	
1	7122	,	USPAT;	2003/12/09 12:47
		328/694.ccls.	US-PGPUB;	
			EPO; JPO;	
2		mo obine tien in about the second	DERWENT	
2	°	ma-ching-tienin. chen-tsung-chuanin. hsu-shew-tsuin.	USPAT;	2003/12/09 12:49
		msu-snew-csuin.	US-PGPUB;	
			EPO; JPO;	
3	19	(((resist photoresist photo-resist)	DERWENT	0000/10/10 10 50
		(photosensitive photo-sensitive (sensitive	USPAT;	2003/12/09 12:50
		near (photo light energy radiation))))	US-PGPUB;	
	ł	near (duv! (deep adj2 (uv ultraviolet	EPO; JPO;	
		ultra-violet ultra adj violet)))) same	DERWENT	
		((oxide dioxide) near (layer film		1
		coating)) same (etchstop etch-stop etch		
		adj stop hardmask hard-mask hard adj mask)		
4	26	(((resist photoresist photo-resist)	HCDAm.	2002/10/22 12 55
-	2.0	(photosensitive photo-sensitive (sensitive	USPAT;	2003/12/09 12:50
		near (photo light energy radiation))))	US-PGPUB;	
	i	with cur\$3) and (((resist photoresist	EPO; JPO;	
		photo-resist) (photosensitive	DERWENT	
		photo-sensitive (sensitive near (photo		
		light energy radiation)))) with ((duv!		
		(deep adj2 (uv ultraviolet ultra-violet		
		ultra adj violet))) (krf arf f2 "f.sub.2")		
		(("157" "193" "248") near (nm! nanometer		
		nano-meter nano adj meter)))) and		
		((etchstop etch-stop etch adj stop		
		hardmask hard-mask hard adj mask) with		
		((si silicon si-contain\$3		1
	•	silicon-contain\$3) ((silicon adj (nitride		
		oxynitride oxy-nitride oxy adj nitride		
		carbide)) "si.sub.3 n.sub.4" sion sic)))		
	i	and ((oxide dioxide) near (layer film		
		coating))		
5	7		USPAT;	2003/12/09 12:51
		(photosensitive photo-sensitive (sensitive	US-PGPUB;	2003/12/09 12:31
	İ	near (photo light energy radiation))))	EPO; JPO;	
		near (duv! (deep adj2 (uv ultraviolet	DERWENT	
		ultra-violet ultra adj violet)))) with	BERNERI	
		cur\$3 with (light radiation)		
6	13	(((duv! (deep adj2 (uv ultraviolet	USPAT	2003/12/09 12:52
		ultra-violet ultra adj violet))) ((uv	1 7 7 7 7 2	2000, 12, 03 12.02
		ultraviolet ultra-violet ultra adj violet)]
)) near3 cur\$3) with temperature with		
		(time seconds! minute)) same (resist		
		photoresist photo-resist)		
8	8673	(duv! uv ultraviolet ultra-violet ultra	USPAT;	2003/12/09 12:53
		adj violet) near3 (resist photoresist	US-PGPUB;	= 100, 15, 03 12.55
		photo-resist)	EPO; JPO;	
			DERWENT	
9	7783	(etchstop etch-stop etch adj stop) near	USPAT;	2003/12/09 12:53
9		(layer film coating material)	US-PGPUB;	2200, 22, 03 12.33
9			EPO; JPO;	
9			, 010,	1
9			DERWENT	i
10	483449	(si-contain\$3 silicon-contain\$3 (silicon	DERWENT USPAT:	2003/12/09 12:55
	483449	(si-contain\$3 silicon-contain\$3 (silicon adj (oxide dioxide nitride)) sio sio2 sin	USPAT;	2003/12/09 12:55
	483449	adj (oxide dioxide nitride)) sio sio2 sin sixny si3n4 "sio.sub.2" "si.sub.3 n.sub.4"	USPAT; US-PGPUB;	2003/12/09 12:55
	483449	adj (oxide dioxide nitride)) sio sio2 sin sixny si3n4 "sio.sub.2" "si.sub.3 n.sub.4"	USPAT; US-PGPUB; EPO; JPO;	2003/12/09 12:55
		<pre>adj (oxide dioxide nitride)) sio sio2 sin sixny si3n4 "sio.sub.2" "si.sub.3 n.sub.4" "si.sub.x n.sub.y")</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	
10	483449 263896	adj (oxide dioxide nitride)) sio sio2 sin sixny si3n4 "sio.sub.2" "si.sub.3 n.sub.4"	USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT;	2003/12/09 12:55
10		<pre>adj (oxide dioxide nitride)) sio sio2 sin sixny si3n4 "sio.sub.2" "si.sub.3 n.sub.4" "si.sub.x n.sub.y")</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	

	[[durat par mitmorried at military and a military a	T	,	
_	adi violet) pear? (regist photon		2003/12/09	12:56
	photo-resist \ come (((ctabates at a bates	1		
	etch add stop) none (leven file section	1 .		
	material)) with ((ci contains)	DERMENT		
	silicon-contains? (silicon add (adda	İ		
'	diovide nitride) cic cic cic cic cic cic cic cic cic c			
	"sio sub ?" "si sub ? n sub 4" "si	1		
	n sub w"\\\ same (oxide neem (lease film	Ì		
	costing material)			
5			0000 (00 (00	
9	adi violet) pear? (regist photograpist		2003/12/09	12:56
	photo-resist) \ same //(otcheter atch atch			
	etch adi ston) near (layor film coating			
	material))) same (oxide near (layor film	DERWENT	İ	
	coating material))			
-5		HCDAT.	2002/10/00	10.07
i	328/694.ccls.) and ((duy! uv ultraviolet		2003/12/09	12:5/
	ultra-violet ultra adi violet) near?		[
	(resist photoresist photo-resist)) and			
	(((etchstop etch-stop etch adi stop) near	DEKWENI		
	(laver film coating material)) same			
	((si-contain\$3 silicon-contain\$3 (silicon			
	adj (oxide dioxide nitride)) sio sio2 sin			
	sixny si3n4 "sio.sub.2" "si_sub 3 n sub 4"			
	"si.sub.x n.sub.v"))) and (oxide near			
	(layer film coating material))			
	j	adj violet) near3 (resist photoresist photo-resist)) same (((etchstop etch-stop etch adj stop) near (layer film coating material)) with ((si-contain\$3 silicon-contain\$3 (silicon adj (oxide dioxide nitride)) sio sio2 sin sixny si3n4 "sio.sub.2" "si.sub.3 n.sub.4" "si.sub.x n.sub.y"))) same (oxide near (layer film coating material)) ((duv! uv ultraviolet ultra-violet ultra adj violet) near3 (resist photoresist photo-resist)) same (((etchstop etch-stop etch adj stop) near (layer film coating material))) same (oxide near (layer film coating material))) same (oxide near (layer film coating material))	adj violet) near3 (resist photoresist photo-resist)) same (((etchstop etch-stop etch adj stop) near (layer film coating material)) with ((si-contain\$3 silicon-contain\$3 (silicon adj (oxide dioxide nitride)) sio sio2 sin sixny si3n4 "sio.sub.2" "si.sub.3 n.sub.4" "si.sub.x n.sub.y"))) same (oxide near (layer film coating material)) ((duv! uv ultraviolet ultra-violet ultra adj violet) near3 (resist photoresist photo-resist)) same (((etchstop etch-stop etch adj stop) near (layer film coating material)) (430/311,313,314,317,327,328,330.ccls. 328/694.ccls.) and ((duv! uv ultraviolet ultra-violet ultra adj violet) near3 (resist photoresist photo-resist)) and (((etchstop etch-stop etch adj stop) near (layer film coating material)) same ((si-contain\$3 silicon-contain\$3 (silicon adj (oxide dioxide nitride)) sio sio2 sin sixny si3n4 "sio.sub.2" "si.sub.3 n.sub.4" "si.sub.x n.sub.y"))) and (oxide near	adj violet) near3 (resist photoresist photo-resist)) same (((etchstop etch-stop etch adj stop) near (layer film coating material)) with ((si-contain\$3 silicon-contain\$3 (silicon adj (oxide dioxide nitride)) sio sio2 sin sixny si3n4 "sio.sub.2" "si.sub.3 n.sub.4" "si.sub.x n.sub.y"))) same (oxide near (layer film coating material)) ((duv! uv ultraviolet ultra-violet ultra adj violet) near3 (resist photoresist photo-resist)) same (((etchstop etch-stop etch adj stop) near (layer film coating material)) (30/311,313,314,317,327,328,330.ccls. 328/694.ccls.) and ((duv! uv ultraviolet ultra-violet ultra-violet ultra-violet ultra adj violet) near3 (resist photoresist photo-resist)) and (((etchstop etch-stop etch adj stop) near (layer film coating material)) same ((si-contain\$3 silicon-contain\$3 (silicon adj (oxide dioxide nitride)) sio sio2 sin sixny si3n4 "sio.sub.2" "si.sub.3 n.sub.4" "si.sub.x n.sub.y"))) and (oxide near